

ABSTRACT OF THE DISCLOSURE

A SiGe-HBT is provided with a SiGe film and a Si film grown in succession by epitaxial growth. The SiGe film is made up of a SiGe buffer layer, a SiGe graded composition layer, and a SiGe upper layer, in which the Ge content is substantially constant or changes not more than that of the SiGe graded composition layer. Even if there are fluctuations in the position of the EB junction, the EB junction is positioned in a portion of the SiGe upper layer, so fluctuations in the Ge content in the EB junction can be inhibited, and a stable high current amplification factor can be obtained. It is also possible to provide a SiGeC film instead of the SiGe film.

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